

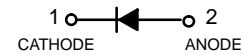
Schottky barrier diode

●Applications

General rectification

●Features

- 1) Small surface mounting type.
- 2) Low V_F , Low I_R
- 3) High reliability.
- 3) We declare that the material of product compliance with RoHS requirements.



●Construction

Silicon epitaxial planar

●Device Marking and Ordering Information

Device	Marking	Shipping
FDR550U	SD	3000/Tape&Reel

●Absolute maximum ratings (Ta = 25°C)

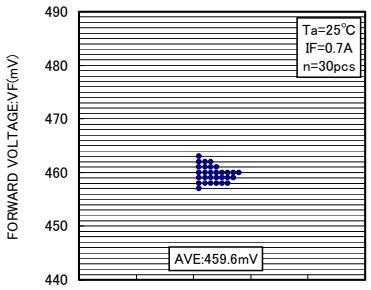
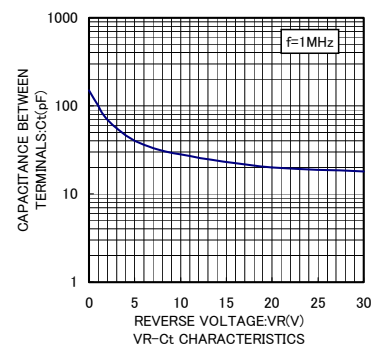
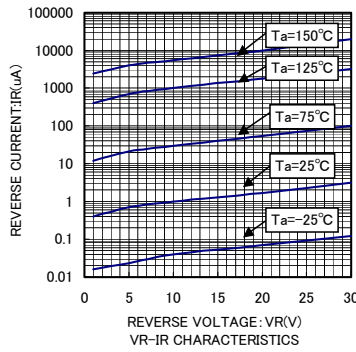
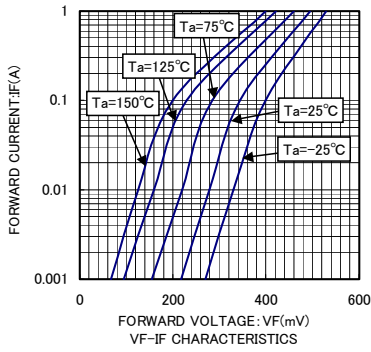
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	1	A
Forward current surge peak *	I_{FSM}	3	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-40 to +150	°C

* 60Hz for 1 \varnothing

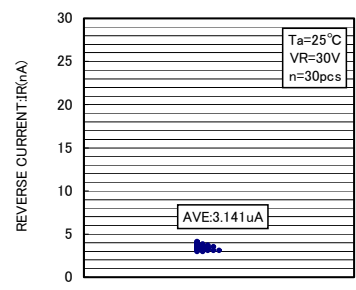
●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	-	-	0.39	V	$I_F=100mA$
	V_{F2}	-	-	0.49	V	$I_F=700mA$
	V_{F3}	-	-	0.52	μA	$I_F=1A$
Reverse current	I_R	-	1	30	μA	$V_R=10V$

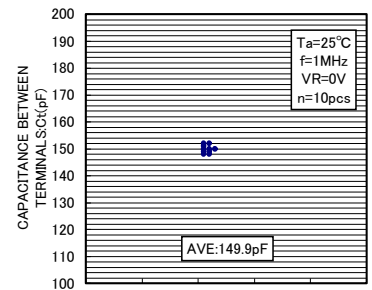
● Electrical characteristic curves (Ta = 25°C)



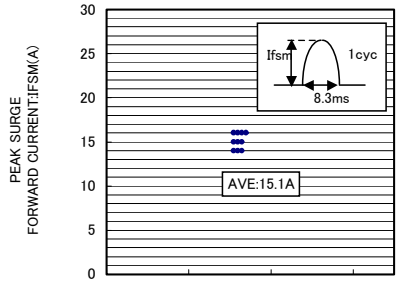
VF DISPERSION MAP



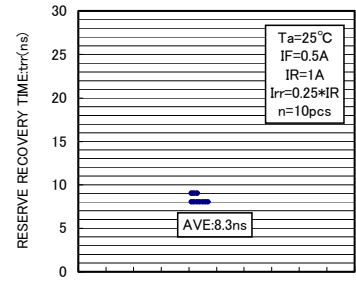
IR DISPERSION MAP



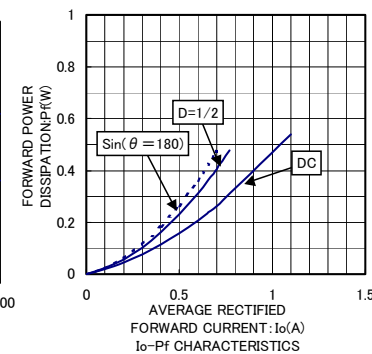
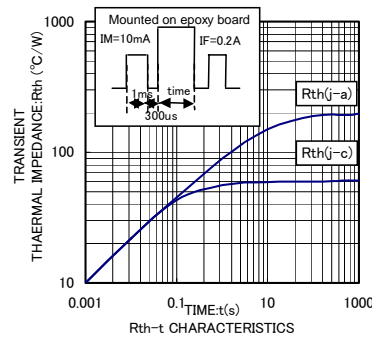
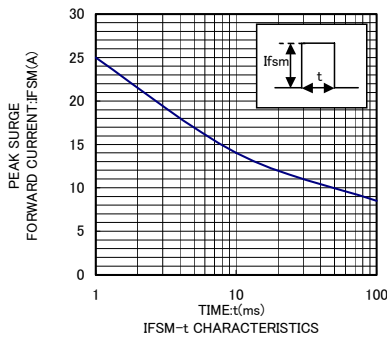
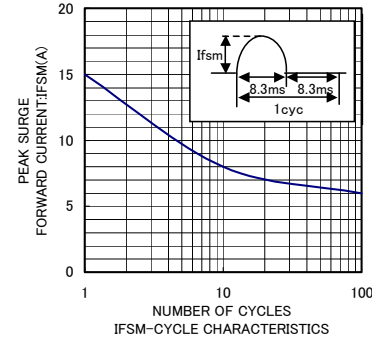
Ct DISPERSION MAP

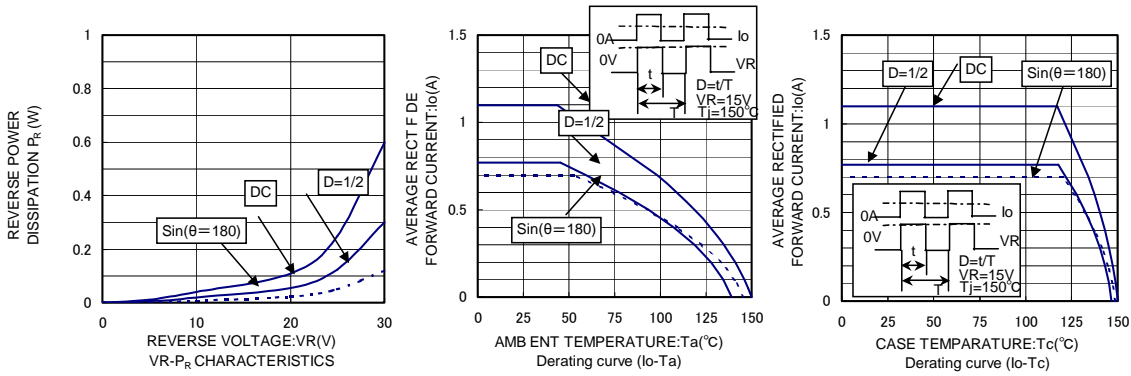


IFSM DISERSION MAP

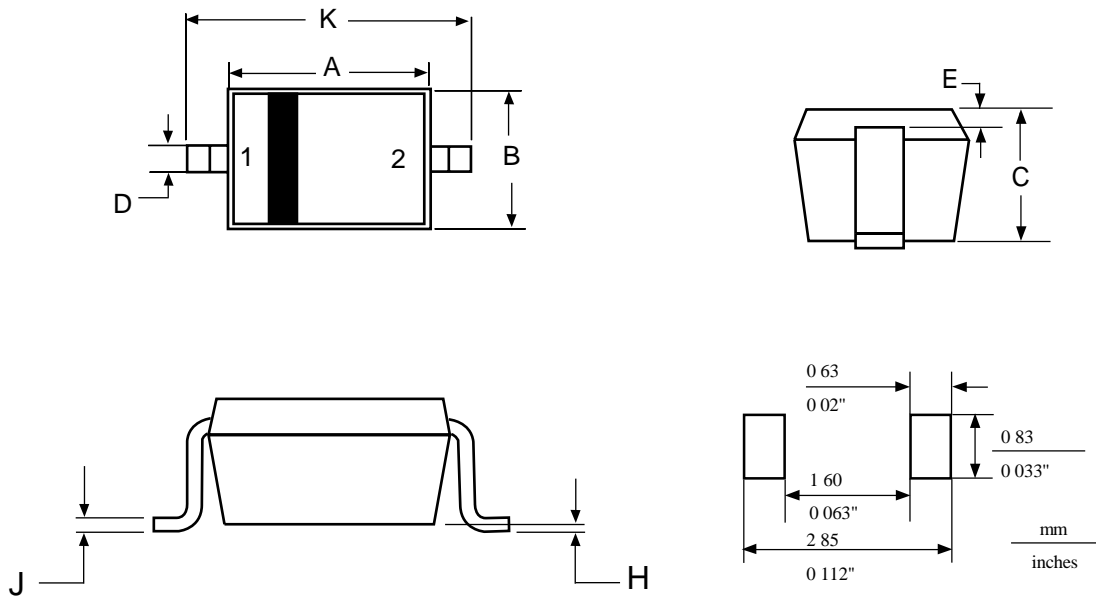


trr DISPERSION MAP





SOD-323



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

PIN: 1. CATHODE
2. ANODE